

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO. YOR920000173US2	SERIAL NO. Not Yet Assigned
Cohen et al.	
FILING Concurrently Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
S	5,102,819	04/07/1992	Matsushita et al.			
S	5,120,666	06/09/1992	Gotou			
S	5,166,084	11/24/1992	Pfiester			
S	5,273,921	12/28/1993	Neudeck et al.			
S	5,371,401	12/06/1994	Kurita			
S	5,461,250	10/24/1995	Burghartz et al.			
S	5,497,019	05/05/1996	Mayer et al.			
S	5,646,058	07/08/1997	Taur et al.			
S	5,708,286	01/13/1998	Uesugi et al.			
S	5,773,331	06/30/1998	Solomon et al.			
S	5,923,963	07/13/1999	Yamanaka			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
S	JP-05-226655	09/1993	Japan				✓

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	"0.18-um Fully-Depleted Silicon-on-Insulator MOSFET's", Min Cao, Ted Kamins, Paul Vande Voorde, Carlos Diaz, and Wayne Greene, IEEE Electron Device Letters, Vol. 18, No. 6, June 1997, pp.251-252		
	"Super Self-Aligned Double-Gate (SSDG) MOSFET's Utilizing Oxidation Rate Difference and Selective Epitaxy", Jong-Ho Lee, Gianni Taraschi, Andy Wei, Tom A. Langdo, Eugene A. Fitzgerald, and Dimitri A. Antoniadis, Microsystems Technology Laboratories, Massachusetts Institute of Technology, Cambridge, MA, IEEE, 1999, pp71-74		

EXAMINER	<i>Shaverdaseh</i>	DATE CONSIDERED	<i>11/27/03</i>
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.